

REMARKS

Figures 1a – 1e have been objected to for failure to include the designation “Prior Art”. Proposed drawing corrections in the form of red-marked drawings are enclosed. Applicants respectfully request approval of the drawing corrections and withdrawal of the objection.

Claim 28 has been rejected under 35 USC 112(1) for including subject matter (nickel) not in the originally filed specification. Applicants note that the originally filed specification includes this subject matter at page 10 lines 5-7. Reconsideration and withdrawal of the rejection under 35 USC 112(1) is respectfully requested.

Claims 1-12, 16, 26, 27, 29, 30 and 32 have been rejected under 35 USC 103(a) as being unpatentable over U.S. patent no. 6,063,677 (“Rodder”) in view of U.S. patent no. 5,937,300 (“Sekine”) and U.S. patent no. 6,051,473 (“Ishida”). Claims 13-15 and 31 have been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, and Ishida, and further in view of U.S. patent 6,054,355 (“Inumiya”). Claims 17-19 have been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, Ishida, and Inumiya and further in view of U.S. patent 6,051,865 (“Gardner”). Claim 28 has been rejected under 35 USC 103(a) as being unpatentable over Rodder, Sekine, and Ishida, and further in view of Wolf. Applicants respectfully traverse these rejections because the cited references do not disclose or suggest every element of any claim, as the following analysis shows.

Claims 26 and 27 have been cancelled, rendering the rejection of these two claims moot.

Claim 1 recites, inter alia, depositing a metal layer over the substrate and the alignment component (emphasis provided). The office action identifies these elements in Rodder as alignment component 120,122, substrate 102, and metal layer 106, shown Figs. 3a,3b and

described at column 3 lines 5-40 of Rodder. However, as shown in Figs. 3a,3b and described in the associated text, the metal layer 106 of Rodder is not deposited over the alignment component 102,122, but is rather placed only to the sides of the alignment component. Sekine, Ishida, Inumiya, Gardner and Wolf do not disclose or suggest this missing claim element. Therefore the cited references, either singly or in combination, do not disclose or suggest every element of claim 1. Claims 2-19 and 28-32 depend from claim 1 and therefore also include the elements not disclosed or suggested by these references.

Various amendments have been made to the claims to better conform to good claim practice and to provide correct dependency in view of the cancelled claims.

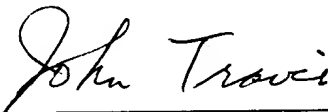
CONCLUSION

For the foregoing reasons, Applicant submits that claims 1-19 and 28-32 are now in condition for allowance, and indication of allowance by the Examiner is respectfully requested. If the Examiner has any questions concerning this application, he or she is requested to telephone the undersigned at the telephone number shown below as soon as possible. No fee is believed due in connection with this amendment. In this is incorrect, please charge any insufficiency or credit any overpayment to Deposit Account No. 02-2666.

Respectfully submitted,

BLAKELY SOLOKOFF TAYLOR & ZAFMAN LLP

Date: 6-12-02



John Travis
Reg. No. 43,203

12400 Wilshire Blvd
Seventh Floor
Los Angeles, California 90025-1026
(512) 330-0844 x644

APPENDIX A

MARKED UP VERSION OF AMENDED CLAIMS:

3. (Amended once) The method of claim 2 wherein the alignment component [is made of] includes a material selected from the group consisting of a silicon oxide and silicon nitride.
4. (Amended once) The method of claim 1 wherein the alignment component [is made of] includes a material which [does not react] is non-reactive with the metal layer when the metal layer is reacted with the semiconductor material of the substrate.
7. (Amended once) The method of claim 1 wherein the metal layer [is] includes material selected from the group consisting of [a material comprising] tungsten, cobalt and titanium.
10. (Amended four times) The method of claim 1 wherein said removing the alignment component [comprises] includes:
- depositing a layer over the silicide regions and the alignment component;
 - planarizing the layer at least until the alignment component is exposed; and
 - etching the alignment component at least until the substrate is exposed to leave an opening between the inner surfaces of the silicide regions to allow for formation of the gate.

11. (Amended twice) The method of claim 10 [wherein, after the etching of the alignment component, the upper portions of the inner surfaces are exposed] further comprising exposing the upper portions of the inner surfaces after said etching of the alignment component.

12. (Amended once) The method of claim 10 wherein the alignment component and the layer are [made] of different materials, one being [made] of [a] silicon oxide and the other being [made] of silicon nitride.

13. (Amended once) The method of claim 1 wherein [the] said replacing with the conductive gate includes [is formed according to a method comprising]:

depositing a gate dielectric layer; and

forming a gate electrode on the gate dielectric layer.

15. (Amended once) The method of claim 13 wherein the gate electrode [is made out of] includes a metal.

18. (Amended once) The method of claim 13 wherein the gate dielectric layer [comprises] includes a material selected from the group consisting of strontium titanate, and barium strontium titanate.

19. (Amended once) The method of claim 17 wherein the gate electrode [comprises] includes a material selected from the group consisting of platinum, a conductive metal oxide, and ruthenium oxide.

28. (Amended once) The method of claim [27] 1, wherein the metal layer [is made of cobalt or] includes nickel and the silicide regions extend partially below the alignment component.

29. (Amended once) The method of claim [27] 1, wherein the alignment component [is made of] includes a material that does not react with the metal layer when the metal layer is reacted with the semiconductor material of the substrate.

30. (Amended once) The method of claim 29, further comprising removing a portion of the metal layer above the alignment component after the metal layer is reacted with the semiconductor material of the substrate.

31. (Amended once) The method of claim [26] 1, wherein the gate dielectric layer is made of silicon oxide and has a thickness of less than 10 Å.

32. (Amended once) The method of claim [26] 1, wherein removing the alignment component comprises:

depositing a layer of a different material than the alignment component over the silicide regions and the alignment component;

planarizing the layer at least until the alignment component is exposed; and

etching the alignment component at least until the substrate and the upper portions of each inner surface of the silicide regions are exposed.